



# STP200NF04 STB200NF04 - STB200NF04-1

N-CHANNEL 40V - 120A TO-220/D<sup>2</sup>PAK/I<sup>2</sup>PAK  
STripFET™ II POWER MOSFET

PRELIMINARY DATA

TYPE	V <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>	P <sub>w</sub>
STP200NF04	40 V	< 0.0037 Ω	120 A	310 W
STB200NF04	40 V	< 0.0037 Ω	120 A	310 W
STB200NF04-1	40 V	< 0.0037 Ω	120 A	310 W

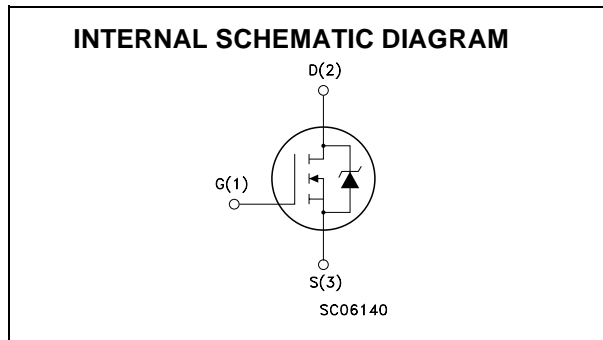
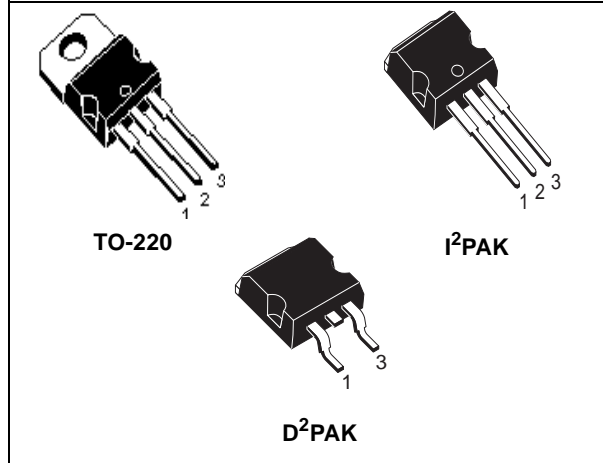
- STANDARD THRESHOLD DRIVE
- 100% AVALANCHE TESTED

## DESCRIPTION

This MOSFET is the latest development of STMicroelectronics unique "Single Feature Size™" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

## APPLICATIONS

- HIGH CURRENT, HIGH SWITCHING SPEED
- AUTOMOTIVE



## ORDERING INFORMATION

SALES TYPE	MARKING	PACKAGE	PACKAGING
STP200NF04	P200NF04	TO-220	TUBE
STB200NF04T4	B200NF04	D <sup>2</sup> PAK	TAPE & REEL
STB200NF04-1	B200NF04	I <sup>2</sup> PAK	TUBE

## STP200NF04 - STB200NF04 - STB200NF04-1

### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V <sub>DS</sub>	Drain-source Voltage (V <sub>GS</sub> = 0)	40	V
V <sub>DGR</sub>	Drain-gate Voltage (R <sub>GS</sub> = 20 kΩ)	40	V
V <sub>GS</sub>	Gate- source Voltage	± 20	V
I <sub>D</sub> (#)	Drain Current (continuous) at T <sub>C</sub> = 25°C	120	A
I <sub>D</sub> (#)	Drain Current (continuous) at T <sub>C</sub> = 100°C	120	A
I <sub>DM</sub> (•)	Drain Current (pulsed)	480	A
P <sub>TOT</sub>	Total Dissipation at T <sub>C</sub> = 25°C	310	W
	Derating Factor	2.07	W/°C
dv/dt (1)	Peak Diode Recovery voltage slope	1.5	V/ns
E <sub>AS</sub> (2)	Single Pulse Avalanche Energy	1.3	J
T <sub>j</sub> T <sub>stg</sub>	Operating Junction Temperature Storage Temperature	-55 to 175	°C

(•) Pulse width limited by safe operating area

(1) I<sub>SD</sub> ≤ 120A, di/dt ≤ 500A/μs, V<sub>DD</sub> ≤ V<sub>(BR)DSS</sub>, T<sub>j</sub> ≤ T<sub>JMAX</sub>.

(2) Starting T<sub>j</sub> = 25°C, I<sub>d</sub> = 60A, V<sub>DD</sub> = 30 V

(#) Current Limited by Package

### THERMAL DATA

		TO-220 / I <sup>2</sup> PAK / D <sup>2</sup> PAK	
R <sub>thj-case</sub>	Thermal Resistance Junction-case Max	0.48	°C/W
R <sub>thj-pcb</sub>	Thermal Resistance Junction-pcb Max	See Curve on page 4	°C/W
R <sub>thj-amb</sub>	Thermal Resistance Junction-ambient (Free air) Max	62.5	°C/W
T <sub>I</sub>	Maximum Lead Temperature For Soldering Purpose	300	°C

### ELECTRICAL CHARACTERISTICS (TCASE = 25°C UNLESS OTHERWISE SPECIFIED)

ON/OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source Breakdown Voltage	I <sub>D</sub> = 250 μA, V <sub>GS</sub> = 0	40			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current (V <sub>GS</sub> = 0)	V <sub>DS</sub> = Max Rating V <sub>DS</sub> = Max Rating, T <sub>C</sub> = 125 °C			1 10	μA μA
I <sub>GSS</sub>	Gate-body Leakage Current (V <sub>DS</sub> = 0)	V <sub>GS</sub> = ± 20V			±100	nA
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	2		4	V
R <sub>DS(on)</sub>	Static Drain-source On Resistance	V <sub>GS</sub> = 10V, I <sub>D</sub> = 90 A			0.0037	Ω

**ELECTRICAL CHARACTERISTICS (CONTINUED)**

**DYNAMIC**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$g_{fs}$ (1)	Forward Transconductance	$V_{DS} = 15\text{ V}, I_D = 90\text{ A}$		150		S
$C_{iss}$ $C_{oss}$ $C_{rss}$	Input Capacitance Output Capacitance Reverse Transfer Capacitance	$V_{DS} = 25\text{ V}, f = 1\text{ MHz}, V_{GS} = 0$		5100 1600 600		pF pF pF

**SWITCHING ON**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ $t_r$	Turn-on Delay Time Rise Time	$V_{DD} = 20\text{ V}, I_D = 90\text{ A}$ $R_G = 4.7\Omega, V_{GS} = 10\text{ V}$ (Resistive Load see, Figure 3)		30 320		ns ns
$Q_g$ $Q_{gs}$ $Q_{gd}$	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD} = 20\text{ V}, I_D = 120\text{ A},$ $V_{GS} = 10\text{ V}$ (see, Figure 4)		170 30 45	210	nC nC nC

**SWITCHING OFF**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$ $t_f$	Turn-off Delay Time Fall Time	$V_{DD} = 20\text{ V}, I_D = 90\text{ A}$ $R_G = 4.7\Omega, V_{GS} = 10\text{ V}$ (Resistive Load see, Figure 3)		140 120		ns ns

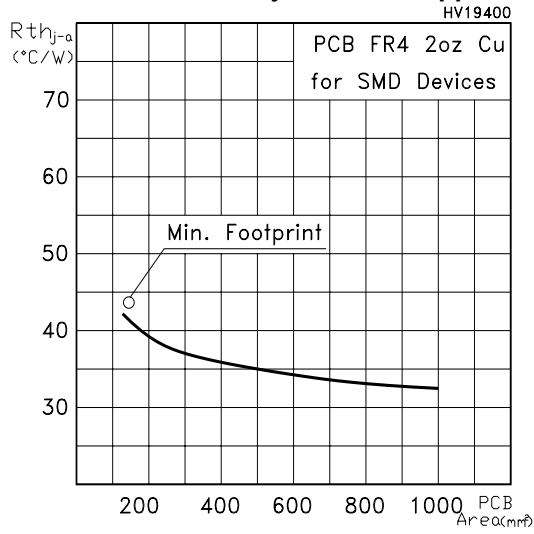
**SOURCE DRAIN DIODE**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{SD}$ $I_{SDM}$ (2)	Source-drain Current Source-drain Current (pulsed)				120 480	A A
$V_{SD}$ (1)	Forward On Voltage	$I_{SD} = 120\text{ A}, V_{GS} = 0$			1.3	V
$t_{rr}$ $Q_{rr}$ $I_{RRM}$	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 120\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 30\text{ V}, T_j = 150^\circ\text{C}$ (see test circuit, Figure 5)		85 190 4.5		ns nC A

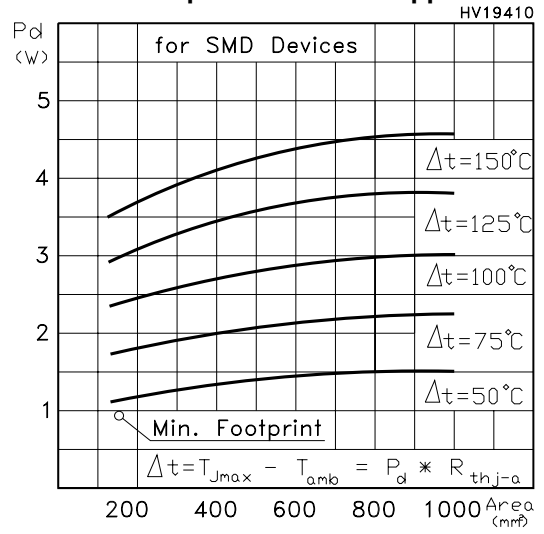
Note: 1. Pulsed: Pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5 %.  
2. Pulse width limited by safe operating area.

**STP200NF04 - STB200NF04 - STB200NF04-1**

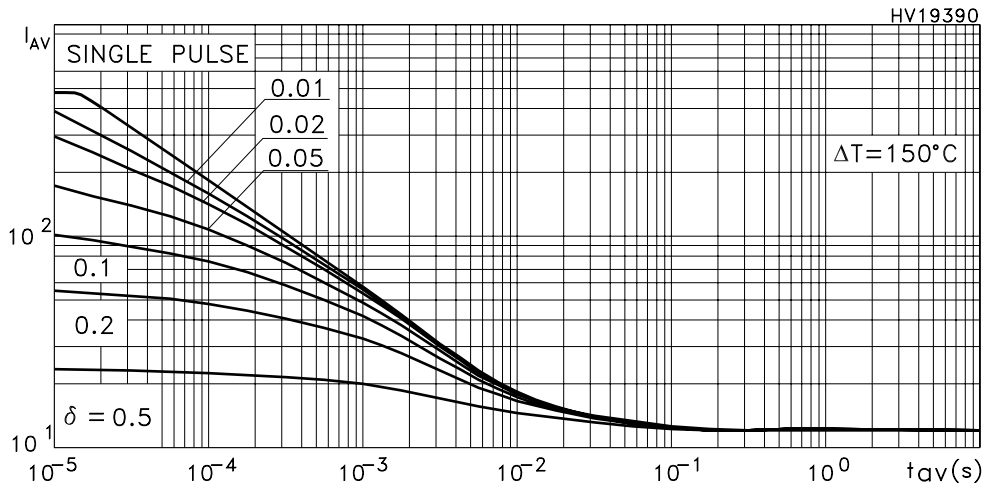
**Thermal Resistance Rthj-a vs PCB Copper Area**



**Max Power Dissipation vs PCB Copper Area**



**Allowable  $I_{AV}$  vs. Time in Avalanche**



The previous curve gives the safe operating area for unclamped inductive loads, single pulse or repetitive, under the following conditions:

$$P_{D(AVE)} = 0.5 * (1.3 * BV_{DSS} * I_{AV})$$

$$E_{AS(AR)} = P_{D(AVE)} * t_{AV}$$

Where:

$I_{AV}$  is the Allowable Current in Avalanche

$P_{D(AVE)}$  is the Average Power Dissipation in Avalanche (Single Pulse)

$t_{AV}$  is the Time in Avalanche

To derate above  $25^\circ C$ , at fixed  $I_{AV}$ , the following equation must be applied:

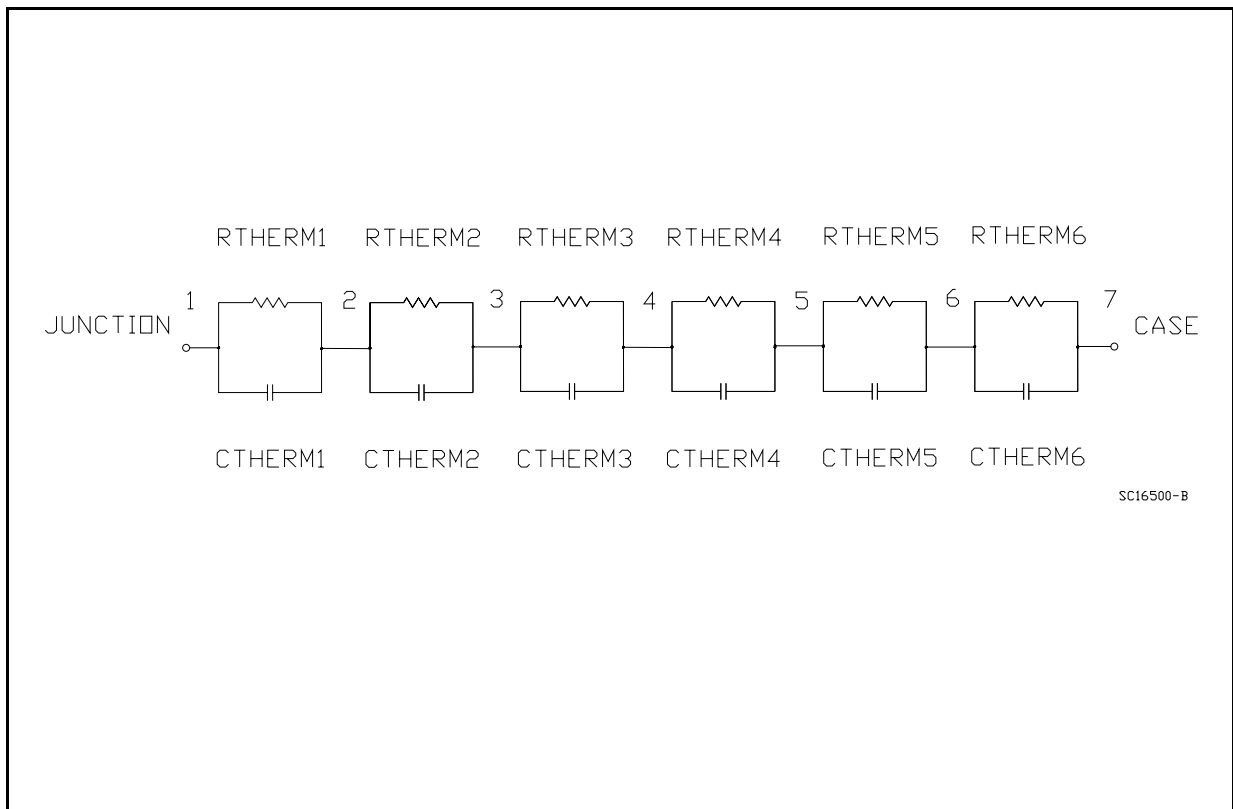
$$I_{AV} = 2 * (T_{jmax} - T_{CASE}) / (1.3 * BV_{DSS} * Z_{th})$$

Where:

$Z_{th} = K * R_{th}$  is the value coming from Normalized Thermal Response at fixed pulse width equal to  $T_{AV}$ .

**SPICE THERMAL MODEL**

Parameter	Node	Value
CTHERM1	1 - 2	1.4958E-3
CTHERM2	2 - 3	3.5074E-2
CTHERM3	3 - 4	5.939E-2
CTHERM4	4 - 5	9.7411E-2
CTHERM5	5 - 6	8.8596E-2
CTHERM6	6 - 7	8.2755E-1
RTHERM1	1 - 2	0.0384
RTHERM2	2 - 3	0.0624
RTHERM3	3 - 4	0.072
RTHERM4	4 - 5	0.0912
RTHERM5	5 - 6	0.1008
RTHERM6	6 - 7	0.1152

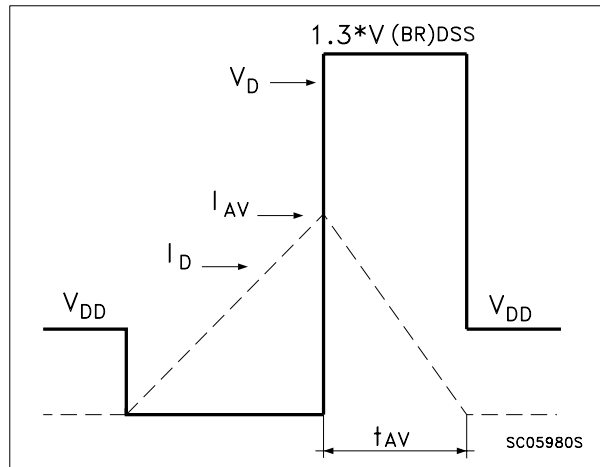


SC16500-B

**Fig. 1: Unclamped Inductive Load Test Circuit**



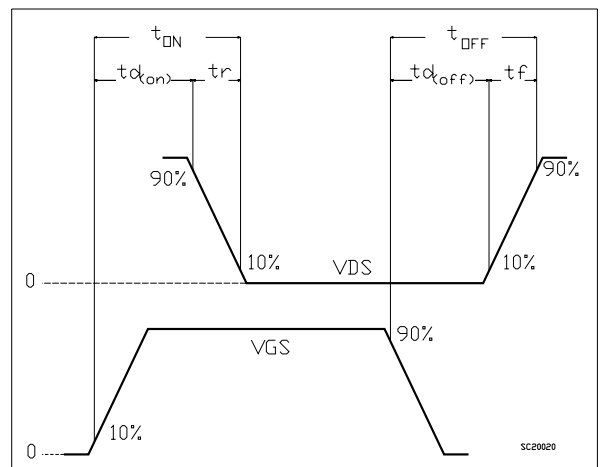
**Fig. 2: Unclamped Inductive Waveform**



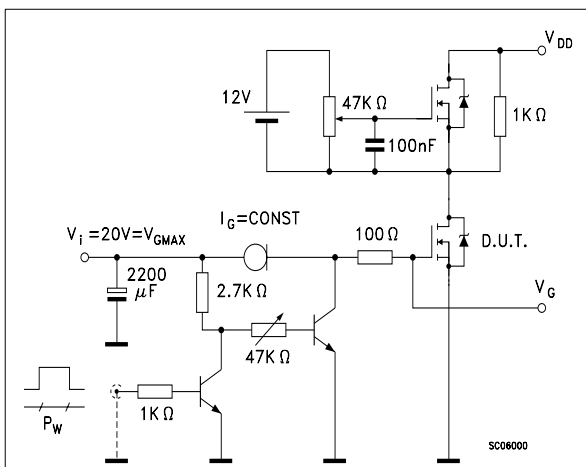
**Fig. 3: Switching Times Test Circuit For Resistive Load**



**Fig. 3.1: Inductive Load Switching And Diode Recovery Times Waveform**



**Fig. 4: Gate Charge test Circuit**



**Fig. 4.1: Gate Charge test Waveform**

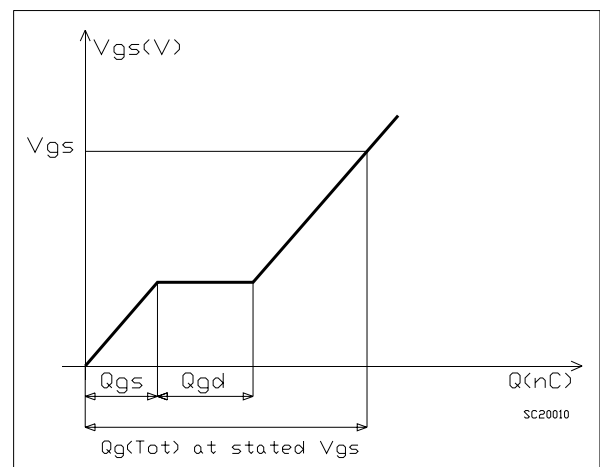


Fig. 5: Test Circuit For Diode Recovery Times

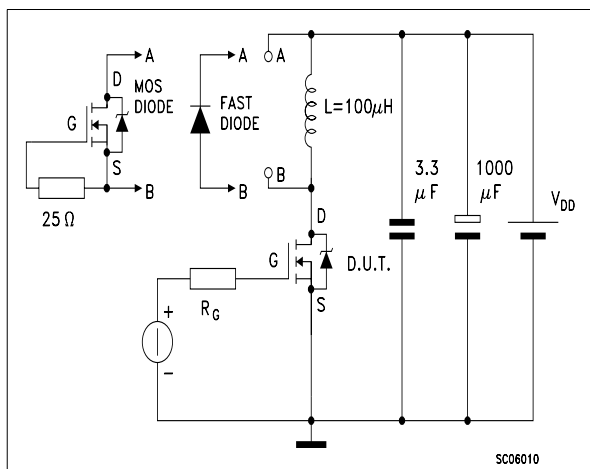
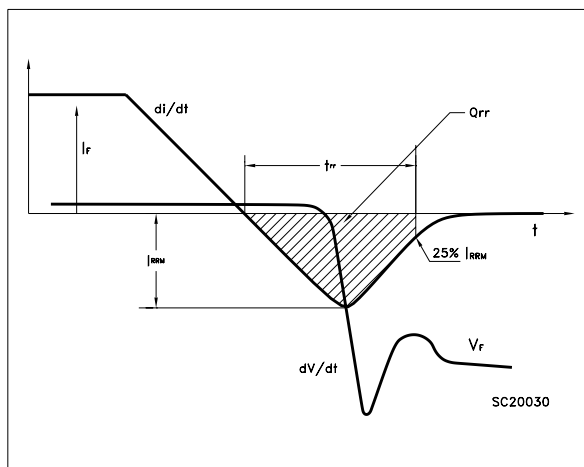


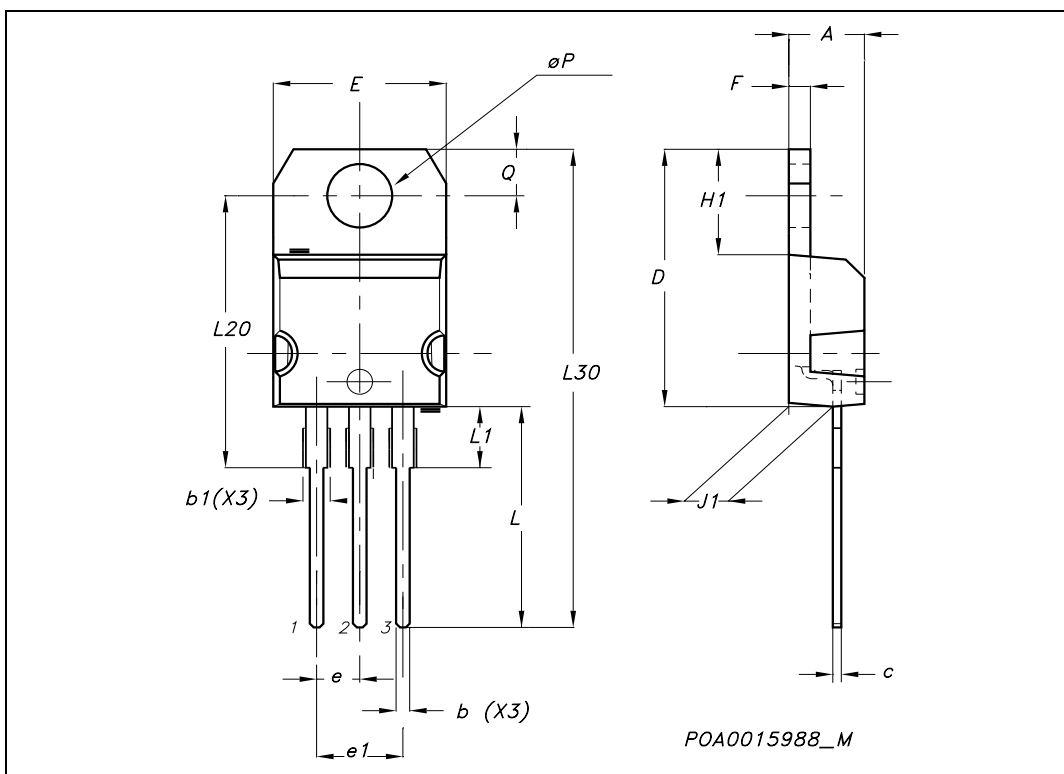
Fig. 5.1: Diode Recovery Times Waveform





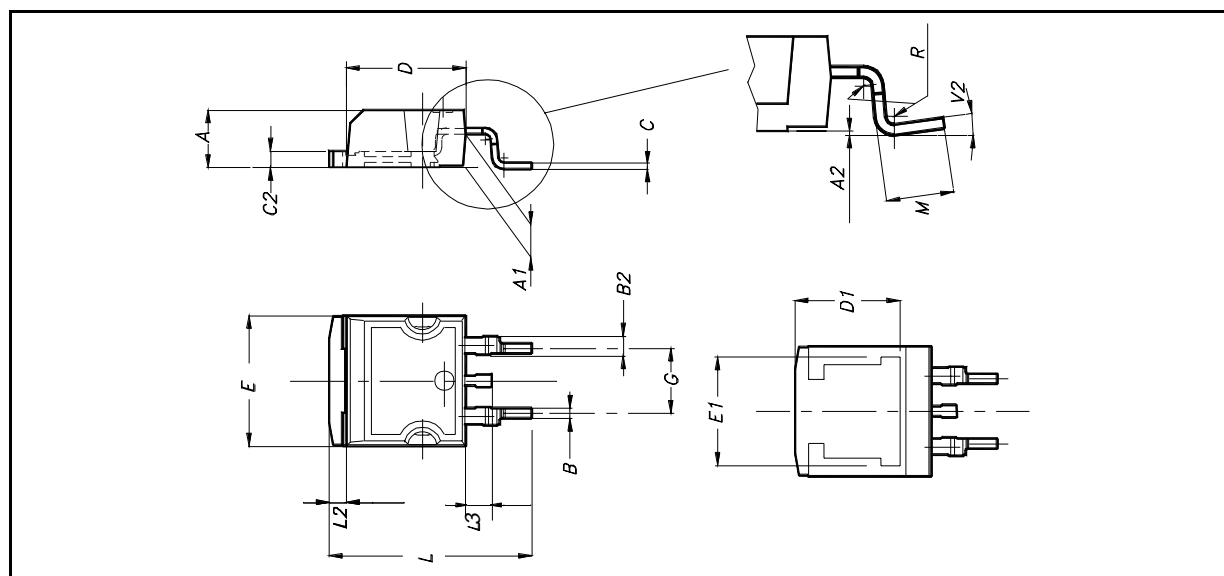
**TO-220 MECHANICAL DATA**

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.15		1.70	0.045		0.066
c	0.49		0.70	0.019		0.027
D	15.25		15.75	0.60		0.620
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.052
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
øP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



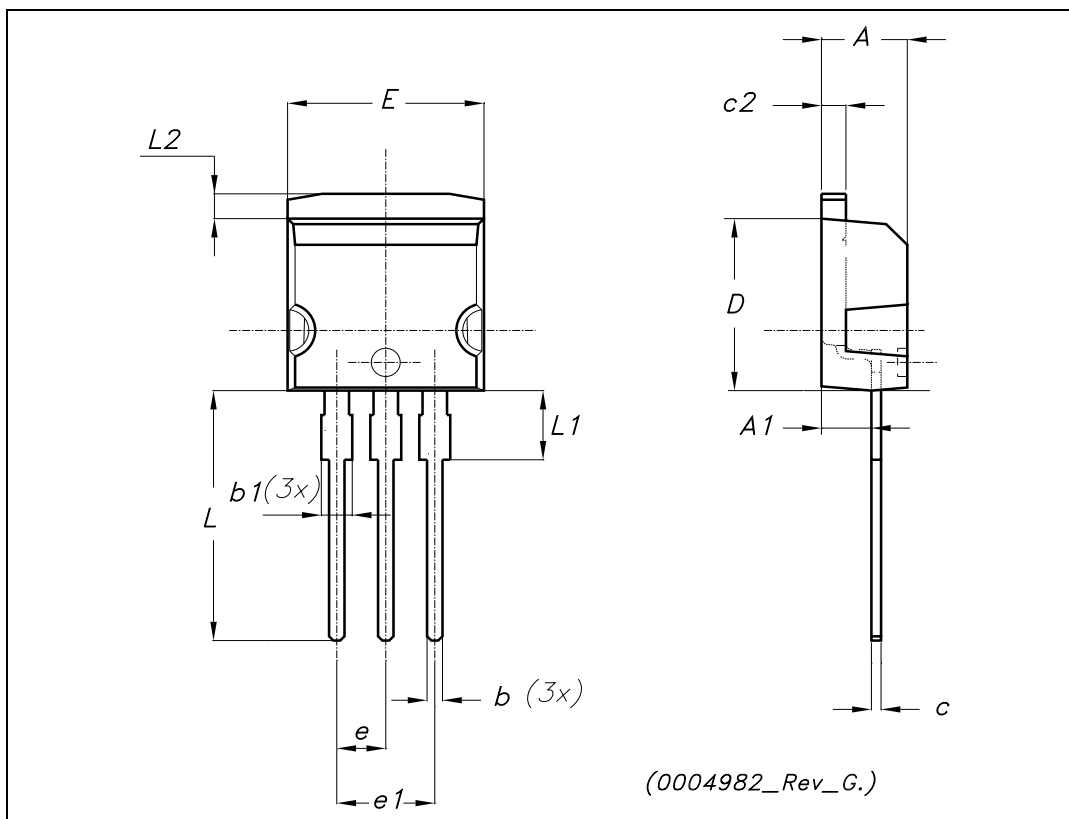
**D<sup>2</sup>PAK MECHANICAL DATA**

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
M	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0°		8°			

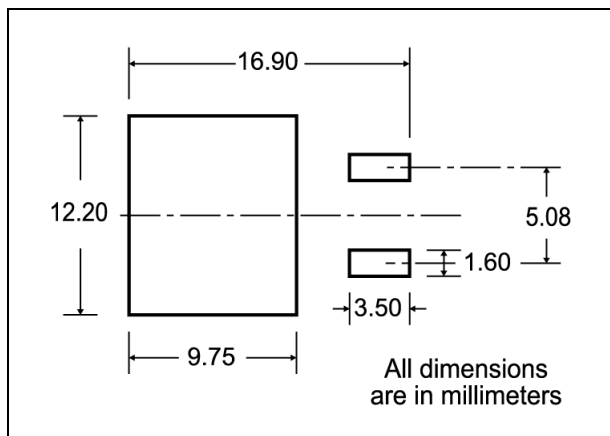


**TO-262 (I<sup>2</sup>PAK) MECHANICAL DATA**

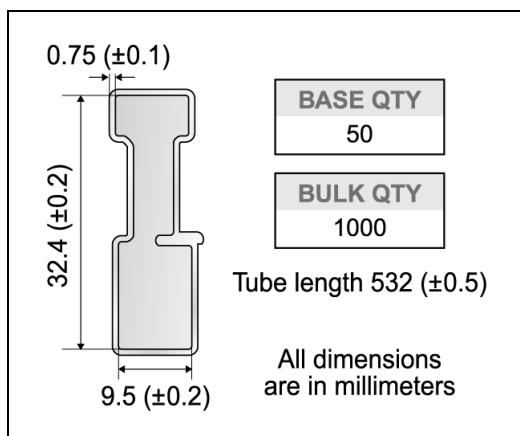
DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
A1	2.40		2.72	0.094		0.107
b	0.61		0.88	0.024		0.034
b1	1.14		1.70	0.044		0.066
c	0.49		0.70	0.019		0.027
c2	1.23		1.32	0.048		0.052
D	8.95		9.35	0.352		0.368
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
E	10		10.40	0.393		0.410
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L2	1.27		1.40	0.050		0.055



### D<sup>2</sup>PAK FOOTPRINT



### TUBE SHIPMENT (no suffix)\*



### TAPE AND REEL SHIPMENT (suffix "T4")\*

Diagram showing the tape mechanical data. It includes a top view of the tape with dimensions A, B, C, D, and a side view with dimensions T, N, and G. A 40 mm min. access hole is shown at the slot location. The tape slot in the core for tape start has a 2.5 mm min. width. The full radius is also indicated.

#### REEL MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0.795	
G	24.4	26.4	0.960	1.039
N	100		3.937	
T		30.4		1.197

BASE QTY	BULK QTY
1000	1000

#### TAPE MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	10.5	10.7	0.413	0.421
B0	15.7	15.9	0.618	0.626
D	1.5	1.6	0.059	0.063
D1	1.59	1.61	0.062	0.063
E	1.65	1.85	0.065	0.073
F	11.4	11.6	0.449	0.456
K0	4.8	5.0	0.189	0.197
P0	3.9	4.1	0.153	0.161
P1	11.9	12.1	0.468	0.476
P2	1.9	2.1	0.075	0.082
R	50		1.574	
T	0.25	0.35	0.0098	0.0137
W	23.7	24.3	0.933	0.956

Diagrams showing the tape and reel shipment details. The top view shows the tape with dimensions K<sub>0</sub>, D, P<sub>2</sub>, P<sub>0</sub>, E, F, W, B<sub>0</sub>, D<sub>1</sub>, A<sub>0</sub>, P<sub>1</sub>, and the center line of the cavity. The side view shows the tape with dimensions T, N, and G. The bottom view shows the tape with dimensions TRL and FEED DIRECTION. The bending radius is labeled as R min.

\* on sales type  
12/13

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